Vishay Siliconix

Precision Monolithic Quad SPST Low-Voltage CMOS Analog Switches

DESCRIPTION

SHAY

The DG441L, DG442L are low voltage pin-for-pin compatible companion devices to the industry standard DG441L, DG442L with improved performance.

Using BiCMOS wafer fabrication technology allows the DG441L, DG442L to operate on single and dual supplies. Single supply voltage ranges from 3 V to 12 V while dual supply operation is recommended with \pm 3 V to \pm 6 V.

Combining high speed (t_{ON}: 20 ns), flat R_{DS(on)} over the analog signal range (5 Ω), minimal insertion lose (- 3 dB at 280 MHz), and excellent crosstalk and off-isolation performance (- 50 dB at 50 MHz), the DG441L, DG442L are ideally suited for audio and video signal switching.

The DG441L, DG442L responds to opposite control logic as shown in the Truth Table open and two normally closed switches.

FEATURES

- Halogen-free according to IEC 61249-2-21 Definition
- 2.7 V thru 12 V single supply or ± 3 V thru ± 6 V dual supply
- On-resistance R_{DS(on)}: 17 Ω
- Fast switching t_{ON}: 20 ns - t_{OFF}: 12 ns
- TTL, CMOS compatible
- Low leakage: 0.25 nA
- 2000 V ESD protection
- Compliant to RoHS Directive 2002/95/EC

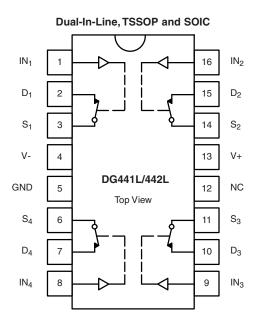
BENEFITS

- Widest dynamic range
- Low signal errors and distortion
- Break-before-make switching action
- Simple interfacing

APPLICATIONS

- Precision automatic test equipment
- Precision data acquisition
- Communication systems
- Battery powered systems
- Computer peripherals
- SDSL, DSLAM
- Audio and video signal routing

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



| TRUTH TABLE | | | | | | | | |
|---------------------|----|-----|--|--|--|--|--|--|
| Logic DG441L DG442L | | | | | | | | |
| 0 | On | Off | | | | | | |
| 1 Off On | | | | | | | | |
| | | | | | | | | |

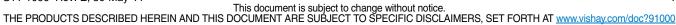
Logic "0" ≤ 0.8 V Logic "1" ≥ 2.4 V

| ORDERING INFORMATION | | | | | | | | |
|----------------------|----------------|------------------------|--|--|--|--|--|--|
| Temp. Range | Package | Part Number | | | | | | |
| | 16-pin TSSOP | DG441LDQ-T1-E3 | | | | | | |
| - 40 °C to 85 °C | 10-pin 1330F | DG442LDQ-T1-E3 | | | | | | |
| - 40 C 10 85 C | 16-pin narrow | DG441LDY-T1-E3 | | | | | | |
| | SOIC | DG442LDY-T1-E3 | | | | | | |
| | 16-pin CerDIP | DG441LAK, DG441LAK/883 | | | | | | |
| - 55 °C to 125 °C | 16-pill CelDIP | DG442LAK, DG442LAK/883 | | | | | | |
| | LCC-20 | DG441LAZ/883 | | | | | | |
| | LCC-20 | DG442LAZ/883 | | | | | | |

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HALOGEN

FREE



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ABSOLUTE MAXIMUM RATINGS ($T_A = 25 \,^{\circ}$ C, unless otherwise noted)

| Parameter | | Symbol | Limit | Unit |
|---|--------------------------------------|--------|--|------|
| V + to V - | | | - 0.3 to 13 | |
| GND to V - A | | | 7 | v |
| Digital Inputs ^a V _S , V _D | | | GND - 0.3 to (V +) + 0.3 or 30 mA, whichever occurs first | |
| Continuous Current (any terminal) | | | 30 | mA |
| Current, S or D (pulsed 1 ms, 10 % duty cycle) | | | 100 | IIIA |
| Storage Temperature | (DQ, DY suffix) | | - 65 to 125 | °C |
| Storage temperature | (AK suffix) | | - 65 to 150 | |
| | 16-pin TSSOP ^c | | 450 | |
| Power Dissipation (Packages) ^b | 16-pin narrow Body SOIC ^d | | 650 | mW |
| | 16-pin CerDIP ^e | | 900 | |

Notes:

a. Signals on S_X , D_X , or IN_X exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings. b. All leads welded or soldered to PC board.

c. Derate 7 mW/°C above 75 °C d. Derate 7.6 mW/°C above 75 °C

e. Derate 12 mW/°C above 75 °C.

| SPECIFICATIONS ^a (Single Supply 12 V) | | | | | | | | | | |
|--|---------------------|--|--------------------|-------------------|--------------------------------------|-------------------|--------------------|-------------------|------|--|
| | | Test Conditions Unless Otherwise Specified V + = 12 V, V - = 0 V | | | A Suffix Limits - 55 °C to 125 °C | | C - 40 °C to 85 °C | | Unit | |
| Parameter | Symbol | V = 12 V, V = 0 V $V_{IN} = 2.4 V, 0.8 V^{f}$ | Temp. ^b | Typ. ^c | Min. ^d | Max. ^d | Min. ^d | Max. ^d | onit | |
| Analog Switch | | | | 1 | | | 1 | | | |
| Analog Signal Range ^e | V _{ANALOG} | | Full | | 0 | 12 | 0 | 12 | V | |
| Drain-Source On-Resistance | R _{DS(on)} | V + = 10.8 V, V - = 0 V $I_{S} = 10 mA, V_{D} = 2/9 V$ | Room Full | 20 | | 30 45 | | 30 40 | 0 | |
| On-Resistance Match Between Channels ^e | $\Delta R_{DS(on)}$ | I _S = 10 mA, V _D = 9 V | Room | 0.1 | | 0.5 | | 0.5 | Ω | |
| Switch Off Leakage Current | I _{S(off)} | V _D = 1/11 V, V _S = 11/1 V | Room Full | | - 1 - 15 | 1 15 | - 1 - 10 | 1 10 | | |
| ownen on Leakage ourrent | I _{D(off)} | | Room Full | | - 1 - 15 | 1 15 | - 1 - 10 | 1 10 | nA | |
| Channel On Leakage Current | I _{D(on)} | $V_{S} = V_{D} = 11/1 V$ | Room Full | | - 1 - 15 | 1 15 | - 1 - 10 | 1 10 | | |
| Digital Control | • | | | | | | | | | |
| Input Current, VIN Low | I _{IL} | V _{IN} Under Test = 0.8 V | Full | 0.01 | - 1.5 | 1.5 | - 1 | 1 | | |
| Input Current, V _{IN} High | I _{IH} | V _{IN} Under Test = 2.4 V | Full | | - 1.5 | 1.5 | - 1 | 1 | μA | |
| Dynamic Characteristics | | | | | | | | | | |
| Turn-On Time | t _{ON} | $R_L = 300 \Omega$, $C_L = 35 pF$ | Room Full | 20 | | 60 80 | | 60 70 | ns | |
| Turn-Off Time | t _{OFF} | $\overline{V}_{S} = 5 V$, see figure 2 | Room Full | 12 | | 35 50 | | 35 45 | ns | |
| Charge Injection ^e | Q | V_g = 0 V, R_g = 0 Ω , C_L = 10 nF | Room | 5 | | | | | рС | |
| Off Isolation ^e | OIRR | $R_1 = 50 \Omega$, $C_1 = 5 pF$, f = 1 MHz | Room | 71 | | | | | dB | |
| Channel-to-Channel Crosstalk ^e | X _{TALK} | $n_{\rm L} = 30.32, 0_{\rm L} = 3.01, 1 = 1.0012$ | Room | 95 | | | | | uБ | |
| Source Off Capacitance ^e | C _{S(off)} | | Room | 5 | | | | | | |
| Drain Off Capacitance ^e | C _{D(off)} | f = 1 MHz | Room | 6 | | | | | pF | |
| Channel On Capacitance ^e | C _{D(on)} | | Room | 15 | | | | | | |
| Power Supplies | • | | | | | • | • | | | |
| Positive Supply Current | l+ | | Full | 0.03 | | 1.5 | | 1 | | |
| Negative Supply Current | I- | V _{IN} = 0 V or 12 V | Room Full | - 0.002 | - 1 - 7.5 | | - 1 - 5 | | μA | |
| Ground Current | I _{GND} | | Full | - 0.002 | - 1.5 | | - 1 | | | |

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Document Number: 71399 S11-1066-Rev. E, 30-May-11



Vishay Siliconix

| SPECIFICATIONS ^a (Dual Supply ± 5 V) | | | | | | | | | |
|--|---------------------|--|--------------------|-------------------|--------------------------------------|-------------------|-------------------|-------------------|------|
| | | Test Conditions Unless Otherwise Specified | | | A Suffix Limits - 55 °C to 125 °C | | | to 85 °C | Unit |
| Parameter | Symbol | V + = 5 V, V - = -5 V $V_{IN} = 2.4 V, 0.8 V^{f}$ | Temp. ^b | Typ. ^c | Min. ^d | Max. ^d | Min. ^d | Max. ^d | onic |
| Analog Switch | | | | | | | | | |
| Analog Signal Range ^e | V _{ANALOG} | | Full | | - 5 | 5 | - 5 | 5 | V |
| Drain-Source On-Resistance | R _{DS(on)} | V + = 5 V, V - = - 5 V I _S = 10 mA, V _D = \pm 3.5 V | Room Full | 20 | | 33 45 | | 33 40 | Ω |
| On-Resistance Match Between Channels ^e | $\Delta R_{DS(on)}$ | $I_{S} = 10 \text{ mA}, V_{D} = \pm 3.5 \text{ V}$ | Room | 0.1 | | 0.5 | | 0.5 | 22 |
| Switch Off | I _{S(off)} | V + = 5.5 , V - = - 5.5 V | Room Full | | - 1 - 15 | 1 15 | - 1 - 10 | 1 10 | |
| Leakage Current ^g | I _{D(off)} | | Room Full | | - 1 - 15 | 1 15 | - 1 - 10 | 1 10 | nA |
| Channel On Leakage Current ^g | I _{D(on)} | V + = 5.5 V, V - = -5.5 V $V_S = V_D = \pm 4.5 V$ | Room Full | | - 1 - 15 | 1 15 | - 1 - 10 | 1 10 | |
| Digital Control | | • | | | | | | | |
| Input Current, V _{IN} Low ^e | IIL | V _{IN} Under Test = 0.8 V | Full | 0.05 | - 1.5 | 1.5 | - 1 | 1 | μA |
| Input Current, V _{IN} High ^e | I _{IH} | V _{IN} Under Test = 2.4 V | Full | 0.05 | - 1.5 | 1.5 | - 1 | 1 | |
| Dynamic Characteristics | | | | | | | | | |
| Turn-On Time | t _{ON} | R _L = 300 Ω, C _L = 35 pF | Room Full | 21 | | 60 83 | | 60 70 | ns |
| Turn-Off Time | t _{OFF} | $V_{S} = \pm 3.5 V$, see figure 2 | Room Full | 16 | | 35 55 | | 35 45 | 115 |
| Charge Injection ^e | Q | $V_g = 0 V$, $R_g = 0 \Omega$, $C_L = 10 nF$ | Room | 5 | | | | | рС |
| Off Isolation ^e | OIRR | | Room | 68 | | | | | |
| Channel-to-Channel Crosstalk ^e | X _{TALK} | $R_L = 50 \ \Omega$, $C_L = 5 \ pF$, f = 1 MHz | Room | 85 | | | | | dB |
| Source Off Capacitance ^e | C _{S(off)} | | Room | 9 | | | | | |
| Drain Off Capacitance ^e | C _{D(off)} | f = 1 MHz | Room | 9 | | | | | pF |
| Channel On Capacitance ^e | C _{D(on)} | | Room | 20 | | | | | |
| Power Supplies | | | | 1 | | 1 | | | |
| Positive Supply Current ^e | l+ | | Full | 0.002 | | 1.5 | | 1 | |
| Negative Supply Current ^e | - | V _{IN} = 0 V or 5 V | Room Full | - 0.002 | - 1 - 7.5 | | - 1 - 5 | | μA |
| Ground Current ^e | I _{GND} | | Full | - 0.002 | - 1.5 | | - 1 | | |

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| SPECIFICATIONS ^a (Single Supply 5 V) | | | | | | | | | |
|--|---------------------|---|---------------------|-------------------|-------------------|-----------------------------|---------------------|-------------------|------|
| | | Test Conditions Unless Otherwise Specified | Otherwise Specified | | | c Limits o 125 °C | D Suffix - 40 °C | to 85 °C | Unit |
| Parameter | Symbol | V + = 5 V, V - = 0 V V _{IN} = 2.4 V, 0.8 V ^f | Temp. ^b | Тур. ^с | Min. ^d | Max. ^d | Min. ^d | Max. ^d | onit |
| Analog Switch | | | | | | | | | |
| Analog Signal Range ^e | V _{ANALOG} | | Full | | | 5 | | 5 | V |
| Drain-Source On-Resistance ^e | R _{DS(on)} | V + = 4.5 V I _S = 5 mA, V _D = 1 V, 3.5 V | Room Full | 35 | | 50 88 | | 50 75 | Ω |
| On-Resistance Match Between Channels ^e | $\Delta R_{DS(on)}$ | I _S = 10 mA, V _D = 3.5 V | Room | 0.5 | | 1 | | 1 | 52 |
| Dynamic Characteristics | | | | | | | | | |
| Turn-On Time ^e | t _{ON} | $R_L = 300 \ \Omega, C_L = 35 \ pF$ | Room Hot | 27 | | 50 90 | | 50 60 | ns |
| Turn-Off Time ^e | t _{OFF} | V_{S} = 3.5 V, see figure 2 | Room Hot | 15 | | 30 55 | | 30 40 | 115 |
| Charge Injection ^e | Q | $V_{g} = 0 V, R_{g} = 0 \Omega, C_{L} = 10 nF$ | Room | 0.5 | | | | | рС |
| Power Supplies | Power Supplies | | | | | | | | |
| Positive Supply Current ^e | l + | | Full | 10 | | 200 | | 100 | |
| Negative Supply Current ^e | ۱- | V _{IN} = 0 V or 5 V | Room Full | - 0.002 | - 1 - 7.5 | | - 1 - 5 | | μA |
| Ground Current ^e | I _{GND} | | Full | - 10 | - 200 | | - 100 | | |



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| SPECIFICATIONS ^a (Single Supply 3 V) | | | | | | | | | |
|--|---------------------|--|--------------------|-------------------|--------------------------------------|-------------------|-------------------------------------|-------------------|--------|
| | | Test Conditions Unless Otherwise Specified | | | A Suffix Limits - 55 °C to 125 °C | | D Suffix Limits - 40 °C to 85 °C | | - Unit |
| Parameter | Symbol | V + = 3 V, V - = 0 V $V_{IN} = 0.4 V^{f}$ | Temp. ^b | Typ. ^c | Min. ^d | Max. ^d | Min. ^d | Max. ^d | onic |
| Analog Switch | | | | | | | | | |
| Analog Signal Range ^e | V _{ANALOG} | | Full | | 0 | 3 | 0 | 3 | V |
| Drain-Source On-Resistance | R _{DS(on)} | V + = 2.7 V, V - = 0 V I _S = 5 mA, V _D = 0.5, 2.2 V | Room Full | 65 | | 80 115 | | 80 100 | Ω |
| On-Resistance Match Between Channels ^e | $\Delta R_{DS(on)}$ | I _S = 5 mA, V _D = 2.2 V | Room | 1 | | 3 | | 3 | 52 |
| Switch Off | I _{S(off)} | V + = 3.3 , V - = 0 V | Room Full | | - 1 - 15 | 1 15 | - 1 - 10 | 1 10 | |
| Leakage Current ^g | I _{D(off)} | V _D = 1, 2 V, V _S = 2, 1 V | Room Full | | - 1 - 15 | 1 15 | - 1 - 10 | 1 10 | nA |
| Channel On Leakage Current ^g | I _{D(on)} | V + = 3.3 V, V - = 0 V $V_S = V_D = 1, 2 V$ | Room Full | | - 1 - 15 | 1 15 | - 1 - 10 | 1 10 | |
| Digital Control | | | | | | | | | |
| Input Current, V _{IN} Low ^e | ۱ _{IL} | V _{IN} under test = 0.4 V | Full | 0.005 | - 1.5 | 1.5 | - 1 | 1 | |
| Input Current, V _{IN} High ^e | I _{IH} | V _{IN} under test = 2.4 V | Full | 0.005 | - 1.5 | 1.5 | - 1 | 1 | μA |
| Dynamic Characteristics | | | | | | | | | |
| Turn-On Time | t _{ON} | R _L = 300 Ω, C _L = 35 pF | Room Full | 50 | | 136 175 | | 136 151 | ns |
| Turn-Off Time | t _{OFF} | V_{S} = 1.5 V, see figure 2 | Room Full | 30 | | 100 140 | | 100 125 | 115 |
| Charge Injection ^e | Q | $V_{g} = 0 V, R_{g} = 0 \Omega, C_{L} = 10 nF$ | Room | 1 | | | | | рС |
| Off Isolation ^e | OIRR | | Room | 68 | | | | | |
| Channel-to-Channel Crosstalk ^e | X _{TALK} | $R_L = 50 $ Ω, $C_L = 5 $ pF , f = 1 MHz | Room | 85 | | | | | dB |
| Source Off Capacitance ^e | C _{S(off)} | | Room | 6 | | | | | |
| Drain Off Capacitance ^e | C _{D(off)} | f = 1 MHz | Room | 6 | | | | | pF |
| Channel On Capacitance ^e | C _{D(on)} | | Room | 20 | | | | | |

Notes:

a. Refer to PROCESS OPTION FLOWCHART.

b. Room = 25 °C, Full = as determined by the operating temperature suffix.

c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.

d. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet.

e. Guaranteed by design, not subject to production test.

f. V_{IN} = input voltage to perform proper function.

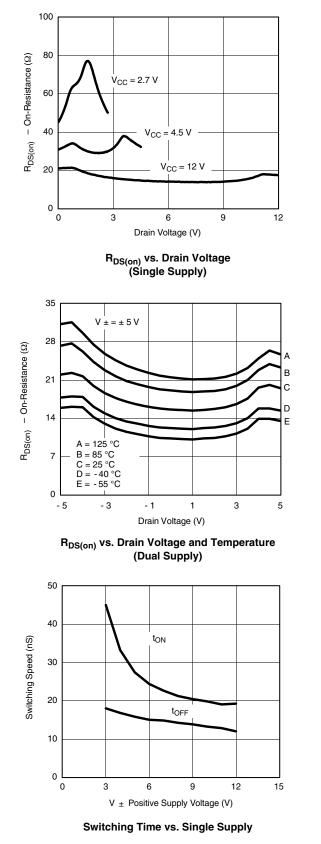
g. Leakage parameters are guaranteed by worst case test conditions and not subject to test.

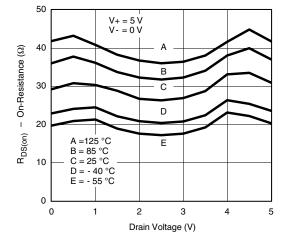
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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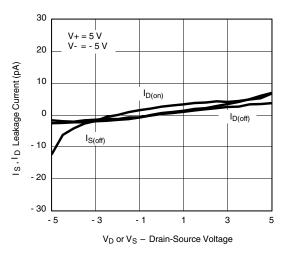
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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

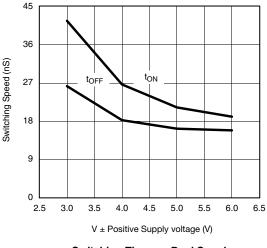




R_{DS(on)} vs. Drain Voltage and Temperature (Single Supply)



Leakage Current vs. Analog Voltage (Dual Supply)



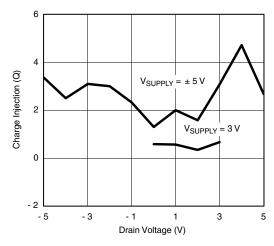
Switching Time vs. Dual Supply

Document Number: 71399 S11-1066–Rev. E, 30-May-11

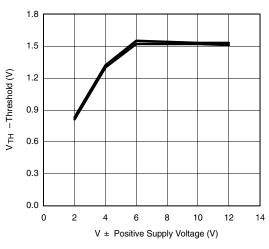


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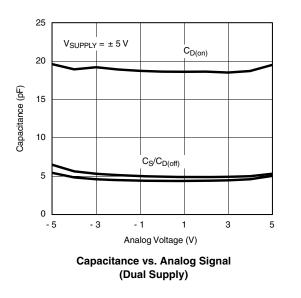
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

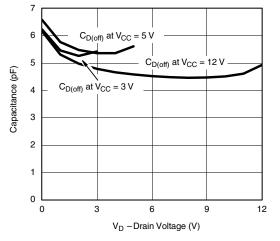


Charge Injection vs. Drain Voltage

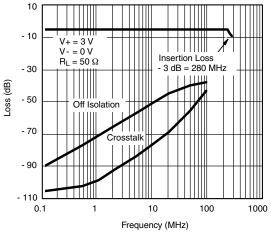


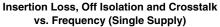
Input Threshold vs. Single Supply Voltage





Drain Capacitance vs. Drain Voltage (Single Supply)





Document Number: 71399 S11-1066–Rev. E, 30-May-11

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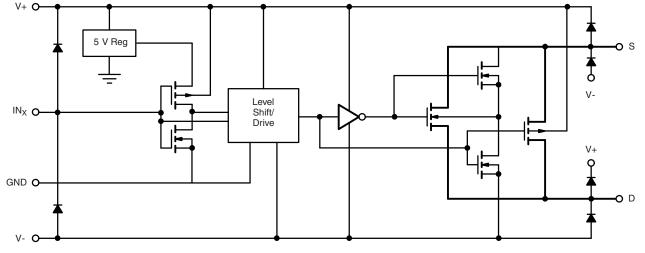
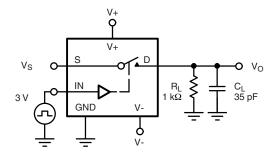
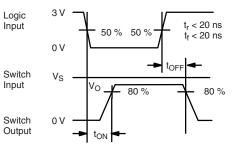


Figure 1.





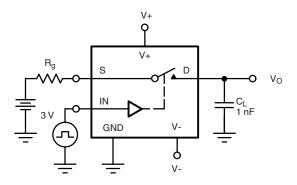
C_L (includes fixture and stray capacitance)



Logic input waveform is inverted for DG442.

Figure 2. Switching Time

Note:



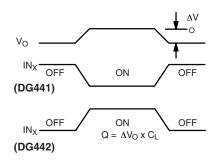


Figure 3. Charge Injection



Document Number: 71399 S11-1066–Rev. E, 30-May-11

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TEST CIRCUITS

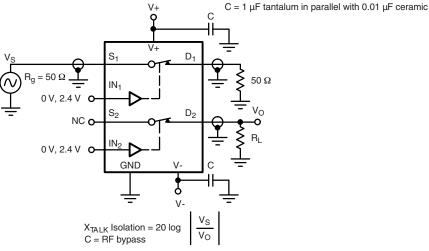
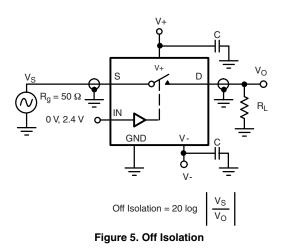


Figure 4. Crosstalk



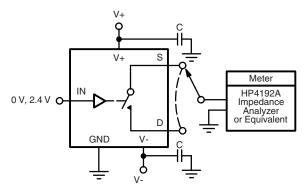


Figure 6. Source/Drain Capacitances

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APPLICATIONS

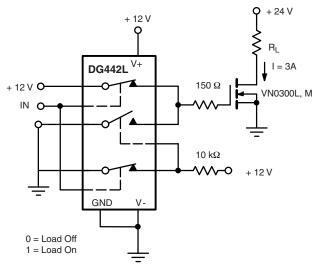
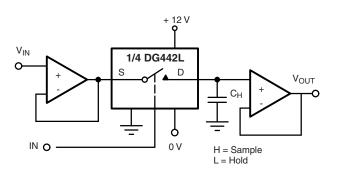
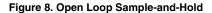
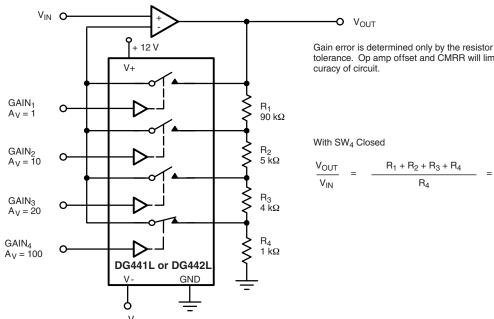


Figure 7. Power MOSFET Driver







tolerance. Op amp offset and CMRR will limit accuracy of circuit.

With SW₄ Closed

• V_{OUT}

$$\frac{OUT}{I_{\rm IN}} = \frac{R_1 + R_2 + R_3 + R_4}{R_4} = 100$$

Figure 9. Precision-Weighted Resistor Programmable-Gain Amplifier

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?71399.

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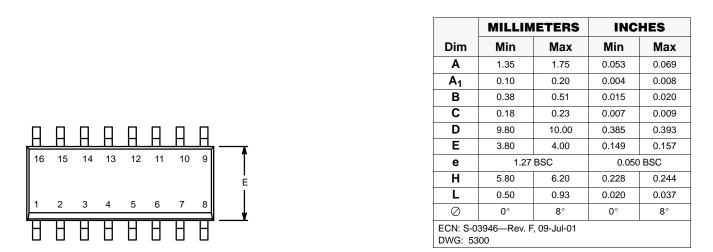
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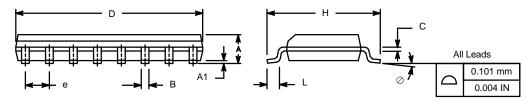




SOIC (NARROW): 16-LEAD

JEDEC Part Number: MS-012



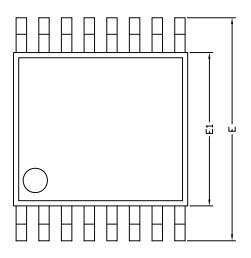


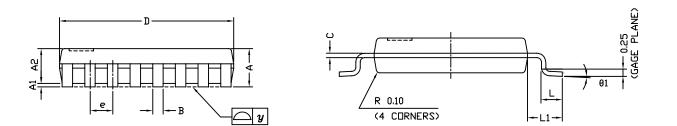


Package Information

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TSSOP: 16-LEAD





| | C | DIMENSIONS IN MILLIMETERS | | | | | | | |
|--------------------------------------|---------|---------------------------|------|--|--|--|--|--|--|
| Symbols | Min | Nom | Мах | | | | | | |
| A | - | 1.10 | 1.20 | | | | | | |
| A1 | 0.05 | 0.10 | 0.15 | | | | | | |
| A2 | - | 1.00 | 1.05 | | | | | | |
| В | 0.22 | 0.28 | 0.38 | | | | | | |
| С | - | 0.127 | - | | | | | | |
| D | 4.90 | 5.00 | 5.10 | | | | | | |
| E | 6.10 | 6.40 | 6.70 | | | | | | |
| E1 | 4.30 | 4.40 | 4.50 | | | | | | |
| е | - | 0.65 | - | | | | | | |
| L | 0.50 | 0.60 | 0.70 | | | | | | |
| L1 | 0.90 | 1.00 | 1.10 | | | | | | |
| у | - | - | 0.10 | | | | | | |
| θ1 | 0° | 3° | 6° | | | | | | |
| ECN: S-61920-Rev. D, 23 DWG: 5624 | -Oct-06 | | | | | | | | |

Application Note 826

Vishay Siliconix



RECOMMENDED MINIMUM PADS FOR SO-16



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index



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